

# HiPerFET™ Power MOSFETs

## ISOPLUS247™

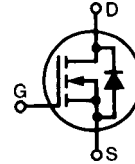
(Electrically Isolated Back Surface)

IXFR 50N50  
IXFR 55N50

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
500 V	43 A	100 mΩ
500 V	48 A	90 mΩ

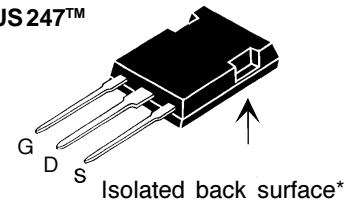
$t_{rr} \leq 250$  ns

Single Die MOSFET



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	50N50 43 55N50 48	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse width limited by $T_{JM}$	50N50 200 55N50 220	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	50N50 50 55N50 55	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	60	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	3	J
dv/dt	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	400	W
$T_J$		-40 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-40 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ min	2500	V~
Weight		5	g

ISOPLUS247™



G = Gate      D = Drain  
S = Source

\* Patent pending

### Features

- Silicon chip on Direct-Copper-Bond substrate
  - High power dissipation
  - Isolated mounting surface
  - 2500V electrical isolation
- Low drain to tab capacitance (<50pF)
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

### Advantages

- Easy assembly
- Space savings
- High power density

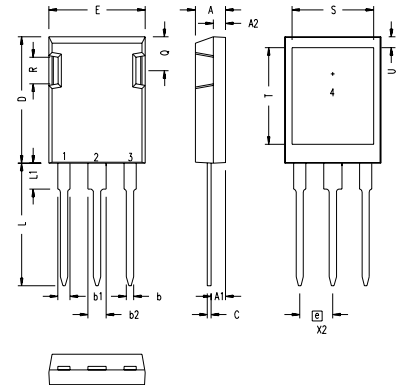
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8\text{ mA}$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0$			$\pm 200\text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		25 $\mu\text{A}$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = I_T$ Note 1	50N50 55N50		100 mΩ 90 mΩ

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.		typ.		max.	
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = I_T$	Note 1			45			S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$				9400			pF
$C_{oss}$					1280			pF
$C_{rss}$					460			pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External),				45			ns
$t_r$					60			ns
$t_{d(off)}$					120			ns
$t_f$					45			ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$				330			nC
$Q_{gs}$					55			nC
$Q_{gd}$					155			nC
$R_{thJC}$							0.30	K/W
$R_{thCK}$					0.15			K/W

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.		typ.		max.	
$I_S$	$V_{GS} = 0\text{ V}$	55N50 50N50			55			A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	55N50 50N50			220			A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$				1.5			V
$t_{rr}$	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$				250			ns
$Q_{RM}$					1.0			$\mu\text{C}$
$I_{RM}$					10			

Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$   
2.  $I_T$  test current: 50N50  $I_T = 25\text{ A}$   
55N50  $I_T = 27.5\text{ A}$

### ISOPLUS 247 OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

**See IXFK55N50 data sheet for characteristic curves.**

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